

# RJF0606JPE

# Silicon N Channel MOS FET Series Power Switching

R07DS0580EJ0100 Rev.1.00 Nov 22, 2011

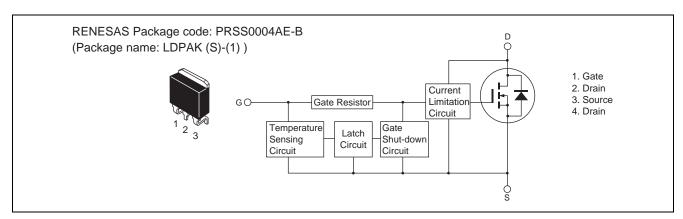
#### **Description**

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

#### **Features**

- Logic level operation (5 V Gate drive).
- Built-in the over temperature shut-down circuit.
- High endurance capability against to the short circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.
- Power supply voltage applies 12 V and 24 V.
- AEC-Q101 Compliant

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	60	V
Gate to source voltage	$V_{GSS}$	16	V
Gate to source voltage	$V_{GSS}$	-2.5	V
Drain current	I <sub>D</sub> Note3	40	Α
Body-drain diode reverse drain current	I <sub>DR</sub>	40	А
Avalanche current	I <sub>AP</sub> Note 2	(12)	А
Avalanche energy	E <sub>AR</sub> Note 2	(617)	mJ
Channel dissipation	Pch Note 1	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at Tc = 25°C

- 2. Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. It provides by the current limitation lower bound value.

# **Typical Operation Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	$V_{IH}$	3.5	_	_	V	
	$V_{IL}$	_	_	1.2	V	
Input current	I <sub>IH1</sub>	1	_	100	μΑ	$Vi = 8 V, V_{DS} = 0$
(Gate non shut down)	I <sub>IH2</sub>	1	_	50	μΑ	$Vi = 3.5 V, V_{DS} = 0$
	I <sub>IL</sub>	1	_	1	μΑ	Vi = 1.2 V, V <sub>DS</sub> = 0
Input current	I <sub>IH(sd)1</sub>	1	0.8	_	mA	$Vi = 8 V, V_{DS} = 0$
(Gate shut down)	I <sub>IH(sd)2</sub>	1	0.35	_	mA	$Vi = 3.5 V, V_{DS} = 0$
Shut down temperature	Tsd	1	175	_	°C	Channel temperature
Gate operation voltage	Vop	3.5	_	12	V	
Drain current	I <sub>D limt</sub>	(40)	_	_	Α	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}^{\text{Note 4}}$
(Current limitation value)						

Note; 4. Pulse test

## **Electrical Characteristics**

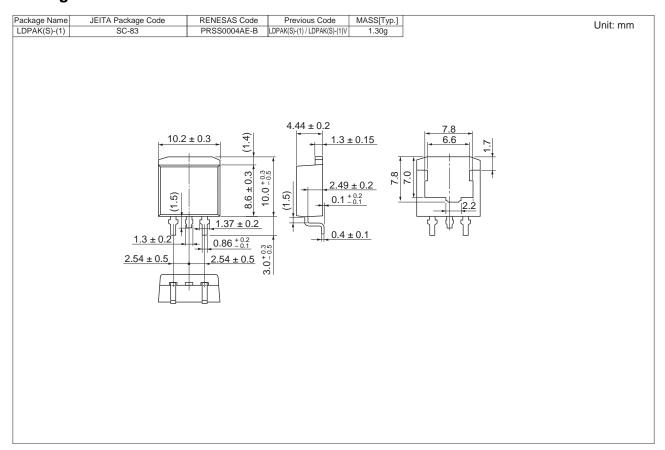
 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current	I <sub>D1</sub>	_	_	(52)	Α	$V_{GS} = 3.5 \text{ V}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
	I <sub>D2</sub>	_	_	(10)	mA	$V_{GS} = 1.2 \text{ V}, V_{DS} = 10 \text{ V}$
	I <sub>D3</sub>	(40)	_	_	Α	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown	$V_{(BR)GSS}$	16	_	_	V	$I_G = 800 \ \mu A, \ V_{DS} = 0$
voltage	V <sub>(BR)GSS</sub>	-2.5	_	_	V	$I_G = -100 \mu A, V_{DS} = 0$
Gate to source leak current	I <sub>GSS1</sub>	_	_	100	μΑ	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I <sub>GSS2</sub>	_	_	50	μΑ	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
	I <sub>GSS3</sub>	_	_	1	μΑ	$V_{GS} = 1.2 \text{ V}, V_{DS} = 0$
	I <sub>GSS4</sub>	_	_	-100	μΑ	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	I <sub>GS(OP)1</sub>	_	0.8	_	mA	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I <sub>GS(OP)2</sub>	_	0.35	_	mA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS1</sub>	_	_	10	μΑ	$V_{DS} = 32 \text{ V}, V_{GS} = 0$
	I <sub>DSS2</sub>	_	_	(10)	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0, \text{ Ta} = 110^{\circ}\text{C}$
Gate to source cutoff voltage	$V_{GS(off)}$	(1.2)	_	(2.4)	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y <sub>fs</sub>	(20)	(38)	_	S	$I_D = 20 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	(16)	25	mΩ	$I_D = 20 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note 5}}$
resistance	R <sub>DS(on)</sub>	_	(12)	(19)	mΩ	$I_D = 20 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 5}}$
Output capacitance	Coss	_	(790)	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{MHz}$
Turn-on delay time	t <sub>d(on)</sub>	_	(14)	_	μS	$V_{GS} = 5 \text{ V}, I_{D} = 20 \text{ A}, R_{L} = 1.5 \Omega$
Rise time	t <sub>r</sub>	_	(68)	_	μS	
Turn-off delay time	$t_{d(off)}$	_	(4.8)	_	μS	
Fall time	t <sub>f</sub>	_	(7.2)	_	μS	
Body-drain diode forward	$V_{DF}$	_	(0.9)	_	V	I <sub>F</sub> = 40 A, V <sub>GS</sub> = 0
voltage						
Body-drain diode reverse	t <sub>rr</sub>	_	(110)	_	ns	$I_F = 40 \text{ A}, V_{GS} = 0$
recovery time						$di_F/dt = 50 A/\mu s$
Over load shut down	t <sub>os1</sub>	_	(0.7)	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$
operation time Note 6	t <sub>os1</sub>		(0.45)	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 24 \text{ V}$

Notes: 5. Pulse test

6. Including the junction temperature rise of the over loaded condition.

# **Package Dimensions**



# **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
RJF0606JPE-00#J3	1000 pcs	Taping

Note: The symbol of a "#" are occasionally presented as a "-".

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